Rino Choi

List of Publications by Year
in descending order

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210	4,455	109137 35	138251 58
papers	citations	h-index	g-index

211	211	211	3239
all docs	docs citations	times ranked	citing authors

#	Article	IF	Citations
1	The effect of moisture on the photon-enhanced negative bias thermal instability in Gaâ€“Inâ€“Znâ€“O thin film transistors. Applied Physics Letters, 2009, 95, .	1.5	289
2	Effect of high-pressure oxygen annealing on negative bias illumination stress-induced instability of InGaZnO thin film transistors. Applied Physics Letters, 2011, 98, .	1.5	257
3	Bonding states and electrical properties of ultrathin HfOxNy gate dielectrics. Applied Physics Letters, 2002, 81, 2593-2595.	1.5	154
4	Mechanism of Electron Trapping and Characteristics of Traps in $hbox{HfO}_{2}$ Gate Stacks. IEEE Transactions on Device and Materials Reliability, 2007, 7, 138-145.	1.5	128
5	Fast transient charging at the graphene/SiO2 interface causing hysteretic device characteristics. Applied Physics Letters, 2011, 98, .	1.5	122
6	Bias-temperature instabilities of polysilicon gate HfO/sub 2/ MOSFETs. IEEE Transactions on Electron Devices, 2003, 50, 1517-1524.	1.6	110
7	The impact of gate dielectric materials on the light-induced bias instability in Hfâ€“Inâ€“Znâ€“O thin film transistor. Applied Physics Letters, 2010, 97, 183503.	1.5	106
8	A Capacitance-Based Methodology for Work Function Extraction of Metals on High-<tex>$kappa$</tex>. IEEE Electron Device Letters, 2004, 25, 420-423.	2.2	104
9	The Electrical and Material Characterization of Hafnium Oxynitride Gate Dielectrics With TaN-Gate Electrode. IEEE Transactions on Electron Devices, 2004, 51, 220-227.	1.6	92
10	Improvement of surface carrier mobility of HfO/sub 2/ MOSFETs by high-temperature forming gas annealing. IEEE Transactions on Electron Devices, 2003, 50, 384-390.	1.6	80
11	Radiation Induced Charge Trapping in Ultrathin ${m HfO}_{2}$-Based MOSFETs. IEEE Transactions on Nuclear Science, 2007, 54, 1883-1890.	1.2	74
12	High-performance TaN/HfSiON/Si metal-oxide-semiconductor structures prepared by NH3 post-deposition anneal. Applied Physics Letters, 2003, 82, 1757-1759.	1.5	69
13	Electron Trap Generation in High-<tex>$kappa$</tex>Gate Stacks by Constant Voltage Stress. IEEE Transactions on Device and Materials Reliability, 2006, 6, 123-131.	1.5	65
14	Pulsed I_{d}â€" V_{g} Methodology and Its Application to Electron-Trapping Characterization and Defect Density Profiling. IEEE Transactions on Electron Devices, 2009, 56, 1322-1329.	1.6	65
15	Improvement in both mobility and bias stability of ZnSnO transistors by inserting ultra-thin InSnO layer at the gate insulator/channel interface. Applied Physics Letters, 2011, 99, .	1.5	63
16	Effect of Pre-Existing Defects on Reliability Assessment of High-K Gate Dielectrics. Microelectronics Reliability, 2004, 44, 1509-1512.	0.9	60
17	The Impact of Device Configuration on the Photon-Enhanced Negative Bias Thermal Instability of GaInZnO Thin Film Transistors. Electrochemical and Solid-State Letters, 2010, 13, H213.	2.2	58
18	Solution-Processable LaZrOx/SiO2 Gate Dielectric at Low Temperature of 180 Â°C for High-Performance Metal Oxide Field-Effect Transistors. ACS Applied Materials & Interfaces, 2014, 6, 18693-18703.	4.0	58

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19	Effects of ALD HfO2 thickness on charge trapping and mobility. Microelectronic Engineering, 2005, 80, 218-221.	1.1	57
20	The Effect of Density-of-State on the Temperature and Gate Bias-Induced Instability of InGaZnO Thin Film Transistors. Journal of the Electrochemical Society, 2010, 157, H983.	1.3	57
21	Metal Electrode/High-k Dielectric Gate-Stack Technology for Power Management. IEEE Transactions on Electron Devices, 2008, 55, 8-20.	1.6	56
22	Achieving High Field-Effect Mobility Exceeding 50 cm<inline-formula> <tex-math notation="TeX">(^{mathrm {2}}) </tex-math></inline-formula>/Vs in In-Zn-Sn-O Thin-Film Transistors. IEEE Electron Device Letters, 2014, 35, 853-855.	2.2	55
23	Characterization of electrically active defects in high-k gate dielectrics by using low frequency noise and charge pumping measurements. Microelectronic Engineering, 2007, 84, 2230-2234.	1.1	54
24	Electrical characterization and material evaluation of zirconium oxynitride gate dielectric in TaN-gated NMOSFETs with high-temperature forming gas annealing. IEEE Transactions on Electron Devices, 2003, 50, 333-340.	1.6	52
25	Improvement in Photo-Bias Stability of High-Mobility Indium Zinc Oxide Thin-Film Transistors by Oxygen High-Pressure Annealing. IEEE Electron Device Letters, 2013, 34, 894-896.	2.2	52
26	Improvement in the device performance of tin-doped indium oxide transistor by oxygen high pressure annealing at 150â€‰Â°C. Applied Physics Letters, 2012, 100, .	1.5	50
27	Ultra-Short Pulse Currentâ€“Voltage Characterization of the Intrinsic Characteristics of High-Îº Devices. Japanese Journal of Applied Physics, 2005, 44, 2437-2440.	0.8	47
28	Structural and electrical properties of HfO2 with top nitrogen incorporated layer. IEEE Electron Device Letters, 2002, 23, 249-251.	2.2	45
29	Electrical and physical characteristics of ultrathin hafnium silicate films with polycrystalline silicon and TaN gates. Applied Physics Letters, 2002, 80, 4416-4418.	1.5	43
30	Validity of constant voltage stress based reliability assessment of high-/spl kappa/ devices. IEEE Transactions on Device and Materials Reliability, 2005, 5, 20-25.	1.5	43
31	Charge trapping and detrapping characteristics in hafnium silicate gate stack under static and dynamic stress. IEEE Electron Device Letters, 2005, 26, 197-199.	2.2	41
32	Evaluation of silicon surface nitridation effects on ultra-thin ZrO2 gate dielectrics. Applied Physics Letters, 2002, 81, 1663-1665.	1.5	40
33	Hot carrier degradation of HfSiON gate dielectrics with TiN electrode. IEEE Transactions on Device and Materials Reliability, 2005, 5, 177-182.	1.5	38
34	A Neuromorphic Device Implemented on a Salmonâ€DNA Electrolyte and its Application to Artificial Neural Networks. Advanced Science, 2019, 6, 1901265.	5.6	38
35	Applications of DCIV method to NBTI characterization. Microelectronics Reliability, 2007, 47, 1366-1372.	0.9	37
36	Comprehensive studies of the degradation mechanism in amorphous InGaZnO transistors by the negative bias illumination stress. Microelectronic Engineering, 2011, 88, 1412-1416.	1.1	36

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37	Thickness dependence of Weibull slopes of HfO2 gate dielectrics. IEEE Electron Device Letters, 2003, 24, 40-42.	2.2	35
38	Highâ€performance Inâ€"Znâ€"O thinâ€film transistors with a soluble processed ZrO₂ gate insulator. Physica Status Solidi - Rapid Research Letters, 2013, 7, 485-488.	1.2	35
39	Area dependence of TDDB characteristics for HfO2 gate dielectrics. IEEE Electron Device Letters, 2002, 23, 594-596.	2.2	34
40	Improved interface quality and charge-trapping characteristics of MOSFETs with high-/spl kappa/ gate dielectric. IEEE Electron Device Letters, 2005, 26, 725-727.	2.2	34
41	A novel approach to characterization of progressive breakdown in high-k/metal gate stacks. Microelectronics Reliability, 2008, 48, 1759-1764.	0.9	34
42	Wakeup-Free and Endurance-Robust Ferroelectric Field-Effect Transistor Memory Using High Pressure Annealing. IEEE Electron Device Letters, 2021, 42, 1295-1298.	2.2	33
43	Comparison of effective work function extraction methods using capacitance and current measurement techniques. IEEE Electron Device Letters, 2006, 27, 598-601.	2.2	32
44	Effect of the Interfacial $hbox{SiO}_{2}$ Layer in High-$k$$ hbox{HfO}_{2}$ Gate Stacks on NBTI. IEEE Transactions on Device and Materials Reliability, 2008, 8, 47-61.	1.5	32
45	A Comprehensive Study on the Effect of TiN Top and Bottom Electrodes on Atomic Layer Deposited Ferroelectric Hf0.5Zr0.5O2 Thin Films. Materials, 2020, 13, 2968.	1.3	30
46	Optimized NH<tex>$_3$</tex>Annealing Process for High-Quality HfSiON Gate Oxide. IEEE Electron Device Letters, 2004, 25, 465-467.	2.2	29
47	Li-Assisted Low-Temperature Phase Transitions in Solution-Processed Indium Oxide Films for High-Performance Thin Film Transistor. Scientific Reports, 2016, 6, 25079.	1.6	28
48	Breakdown characteristics of nFETs in inversion with metal/HfO2 gate stacks. Microelectronic Engineering, 2008, 85, 27-35.	1.1	27
49	Electric-field-driven dielectric breakdown of metal-insulator-metal hafnium silicate. Applied Physics Letters, 2007, 91, .	1.5	26
50	Charge trapping and detrapping characteristics in hafnium silicate gate dielectric using an inversion pulse measurement technique. Applied Physics Letters, 2005, 87, 122901.	1.5	25
51	High Performance Metal Oxide Field-Effect Transistors with a Reverse Offset Printed Cu Source/Drain Electrode. ACS Applied Materials & Interfaces, 2016, 8, 1156-1163.	4.0	25
52	Effects of varying interfacial oxide and high-k layer thicknesses for HfO2 metalâ€"oxideâ€"semiconductor field effect transistor. Applied Physics Letters, 2004, 85, 1286-1288.	1.5	24
53	The Effect of Interfacial Dipoles on the Metal-Double Interlayers-Semiconductor Structure and Their Application in Contact Resistivity Reduction. ACS Applied Materials & Interfaces, 2016, 8, 35614-35620.	4.0	24
54	Effect of Li-doping on low temperature solution-processed indiumâ€"zinc oxide thin film transistors. Thin Solid Films, 2017, 641, 19-23.	0.8	24

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55	Oxidation behaviour and strength of B4C-30 wt% SiC composite materials. Journal of Materials Science, 1995, 30, 3897-3902.	1.7	23
56	Ti-Doped Indium Tin Oxide Thin Films for Transparent Field-Effect Transistors: Control of Charge-Carrier Density and Crystalline Structure. ACS Applied Materials & Interfaces, 2011, 3, 2522-2528.	4.0	23
57	A Novel Bias Temperature Instability Characterization Methodology for High-knMOSFETs. IEEE Electron Device Letters, 2006, 27, 849-851.	2.2	22
58	PBTI-Associated High-Temperature Hot Carrier Degradation of nMOSFETs With Metal-Gate/High- k Dielectrics. IEEE Electron Device Letters, 2008, 29, 389-391.	2.2	22
59	Investigation of Light-Induced Bias Instability in Hf-In-Zn-O Thin Film Transistors: A Cation Combinatorial Approach. Journal of the Electrochemical Society, 2011, 158, H433.	1.3	22
60	Facile one-step synthesis of magnesium-doped ZnO nanoparticles: optical properties and their device applications. Journal Physics D: Applied Physics, 2013, 46, 285101.	1.3	22
61	Performance Improvement of p-Channel Tin Monoxide Transistors With a Solution-Processed Zirconium Oxide Gate Dielectric. IEEE Electron Device Letters, 2017, 38, 1543-1546.	2.2	22
62	Nickel-silicide phase effects on flatband voltage shift and equivalent oxide thickness decrease of hafnium silicon oxynitride metal-silicon-oxide capacitors. Applied Physics Letters, 2005, 86, 222906.	1.5	21
63	Effects of high temperature forming gas anneal on the characteristics of metal-oxide-semiconductor field-effect transistor with HfO2 gate stack. Applied Physics Letters, 2004, 84, 4839-4841.	1.5	19
64	Hot carrier degradation in HfSiONâˆ•TiN fin shaped field effect transistor with different substrate orientations. Journal of Vacuum Science & Technology B, 2009, 27, 468.	1.3	19
65	Gate Engineering in TiN/La/TiN and TiLaN Metal Layers on Atomic-Layer-Deposited $hbox{HfO}_{2}/hbox{Si}$. IEEE Electron Device Letters, 2012, 33, 955-957.	2.2	19
66	High performance solution processed zirconium oxide gate dielectric appropriate for low temperature device application. Thin Solid Films, 2015, 589, 90-94.	0.8	19
67	Effects of deuterium anneal on MOSFETs with HfO2 gate dielectrics. IEEE Electron Device Letters, 2003, 24, 144-146.	2.2	18
68	Highly manufacturable advanced gate-stack technology for sub-45-nm self-aligned gate-first CMOSFETs. IEEE Transactions on Electron Devices, 2006, 53, 979-989.	1.6	18
69	Effects of metal gate-induced strain on the performance of metal-oxide-semiconductor field effect transistors with titanium nitride gate electrode and hafnium oxide dielectric. Applied Physics Letters, 2007, 91, .	1.5	18
70	Electrical characterization and analysis techniques for the high-Îº era. Microelectronics Reliability, 2007, 47, 479-488.	0.9	18
71	Transient Charging and Relaxation in High-k Gate Dielectrics and Their Implications. Japanese Journal of Applied Physics, 2005, 44, 2415-2419.	0.8	17
72	Electrical observation of deep traps in high-/spl kappa//metal gate stack transistors. IEEE Electron Device Letters, 2005, 26, 839-841.	2.2	17

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73	Stress field analysis to understand the breakdown characteristics of stacked high-k dielectrics. Applied Physics Letters, 2009, 94, 162904.	1.5	17
74	Effects of composition and thickness of TiN metal gate on the equivalent oxide thickness and flat-band voltage in metal oxide semiconductor devices. Microelectronic Engineering, 2013, 109, 160-162.	1.1	17
75	Electrical performance enhancement of p-type tin oxide channel thin film transistor using aluminum doping. Thin Solid Films, 2017, 641, 24-27.	0.8	17
76	High-quality ultra-thin HfO/sub 2/ gate dielectric MOSFETs with TaN electrode and nitridation surface preparation. , 0, , .		16
77	Effect of $hbox{F}_{2}$ Postmetallization Annealing on the Electrical and Reliability Characteristics of HfSiO Gate Dielectric. IEEE Electron Device Letters, 2007, 28, 21-23.	2.2	16
78	Effects of Film Stress Modulation Using TiN Metal Gate on Stress Engineering and Its Impact on Device Characteristics in Metal Gate/High-k Dielectric SOI FinFETs. IEEE Electron Device Letters, 2008, 29, 487-490.	2.2	16
79	One-step fabrication and characterization of silica-sheathed ITO nanowires. Journal of Solid State Chemistry, 2010, 183, 2490-2495.	1.4	16
80	Remote plasma atomic layer deposited Al2O3 4H SiC MOS capacitor with remote H2 plasma passivation and post metallization annealing. Microelectronic Engineering, 2015, 147, 239-243.	1.1	16
81	Influence of Fast Charging on Accuracy of Mobility in ${a}$ -InHfZnO Thin-Film Transistor. IEEE Electron Device Letters, 2017, 38, 203-206.	2.2	16
82	Low-Temperature Solution-Based In₂O₃ Channel Formation for Thin-Film Transistors Using a Visible Laser-Assisted Combustion Process. IEEE Electron Device Letters, 2017, 38, 1259-1262.	2.2	16
83	Decoupling of cold-carrier effects in hot-carrier reliability assessment of HfO/sub 2/ gated nMOSFETs. IEEE Electron Device Letters, 2006, 27, 662-664.	2.2	15
84	Application of Single-Pulse Charge Pumping Method on Evaluation of Indium Gallium Zinc Oxide Thin-Film Transistors. IEEE Transactions on Electron Devices, 2018, 65, 3786-3790.	1.6	15
85	Effects of grain boundaries on conversion efficiencies of single-crystal-like GaAs thin-film solar cells on flexible metal tapes. Solar Energy Materials and Solar Cells, 2019, 199, 122-128.	3.0	15
86	Incremental Drain-Voltage-Ramping Training Method for Ferroelectric Field-Effect Transistor Synaptic Devices. IEEE Electron Device Letters, 2022, 43, 17-20.	2.2	15
87	Trapping/De-Trapping Gate Bias Dependence of Hf-Silicate Dielectrics with Poly and TiN Gate Electrode. Japanese Journal of Applied Physics, 2005, 44, 2420-2423.	0.8	14
88	Interfacial and electrical properties of HfO₂ gate dielectrics grown on GaAs by atomic layer deposition using different oxidants. Journal Physics D: Applied Physics, 2012, 45, 435305.	1.3	14
89	Probing stress effects in HfO2 gate stacks with time dependent measurements. Microelectronics Reliability, 2005, 45, 806-810.	0.9	13
90	An Accurate Câ€“ V Measurement Method for Highly Leaky Devicesâ€"Part I. IEEE Transactions on Electron Devices, 2008, 55, 2429-2436.	1.6	13

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91	Electrical Characterization of the Self-Heating Effect in Oxide Semiconductor Thin-Film Transistors Using Pulse-Based Measurements. IEEE Transactions on Electron Devices, 2018, 65, 2492-2497.	1.6	13
92	Effects of dielectric structure of HfO2 on carrier generation rate in Si substrate and channel mobility. Applied Physics Letters, 2004, 84, 2148-2150.	1.5	12
93	Relaxation of FN stress induced V/sub th/ shift at NMOSFETs with HfSiON gate dielectric and TiN gate electrode. , 0, , .		12
94	Extraction of the Threshold-Voltage Shift by the Single-Pulse Technique. IEEE Electron Device Letters, 2007, 28, 734-736.	2.2	12
95	The Effect of Nanoscale Nonuniformity of Oxygen Vacancy on Electrical and Reliability Characteristics of $hbox{HfO}_{2}$ MOSFET Devices. IEEE Electron Device Letters, 2008, 29, 54-56.	2.2	12
96	Demonstration of High-Performance PMOSFETs Using $ hbox{Si}$â€“$hbox{Si}_{x}hbox{Ge}_{1 - x}$ â€“$hbox{Si}$ Quantum Wells With High- $kappa$/Metal-Gate Stacks. IEEE Electron Device Letters, 2008, 29, 99-101.	2.2	12
97	Contribution of Interface States and Oxide Traps to the Negative Bias Temperature Instability of High-k pMOSFETs. IEEE Electron Device Letters, 2009, 30, 291-293.	2.2	12
98	A strategy to boost external quantum efficiency of organic light-emitting transistors. Applied Physics Letters, 2019, 115, .	1.5	12
99	Low Temperature Thermal Atomic Layer Deposition of Aluminum Nitride Using Hydrazine as the Nitrogen Source. Materials, 2020, 13, 3387.	1.3	12
100	Characterization of fast charge trapping in bias temperature instability in metal-oxide-semiconductor field effect transistor with high dielectric constant. Applied Physics Letters, 2010, 96, 142110.	1.5	11
101	Investigation of co-sputtered LiZnSnO thin film transistors. Thin Solid Films, 2012, 522, 435-440.	0.8	11
102	Intrinsic Time Zero Dielectric Breakdown Characteristics of HfAlO Alloys. IEEE Transactions on Electron Devices, 2013, 60, 3683-3689.	1.6	11
103	Non-Alloyed Ohmic Contacts on GaAs Using Metal-Interlayer-Semiconductor Structure With SF₆Plasma Treatment. IEEE Electron Device Letters, 2016, 37, 373-376.	2.2	11
104	Performance of polysilicon gate HfO2 MOSFETs on [100] and [111] silicon substrates. IEEE Electron Device Letters, 2003, 24, 254-256.	2.2	10
105	Suppression in negative bias illumination stress instability of zinc tin oxide transistor by insertion of thermal TiOxfilms. IEEE Electron Device Letters, 2013, 34, 253-255.	2.2	10
106	Effect of High Pressure Hydrogen or Deuterium Anneal on Polysilicon Channel Field Effect Transistors. Journal of Nanoscience and Nanotechnology, 2016, 16, 10341-10345.	0.9	10
107	Double-gate thin film transistor with suspended-gate applicable to tactile force sensor. Nano Convergence, 2020, 7, 31.	6.3	10
108	High performance thin film transistors using low-temperature solution-processed Li-incorporated In2O3/ZrO2 stacks. Microelectronic Engineering, 2015, 147, 27-30.	1.1	9

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109	Improving Electrical Stability of a-InGaZnO Thin-Film Transistors with Thermally Deposited Self-Assembled Monolayers. Electronic Materials Letters, 2020, 16, 451-456.	1.0	9
110	Scaling down of ultrathin HfO[sub 2] gate dielectrics by using a nitrided Si surface. Journal of Vacuum Science & Technology an Official Journal of the American Vacuum Society B, Microelectronics Processing and Phenomena, 2004, 22, 916.	1.6	8
111	Accurate Series-Resistance Extraction From Capacitor Using Time Domain Reflectometry. IEEE Electron Device Letters, 2007, 28, 279-281.	2.2	8
112	H₂ High Pressure Annealed Y-Doped ZrO₂ Gate Dielectric With an EOT of 0.57 nm for Ge MOSFETs. IEEE Electron Device Letters, 2019, 40, 1350-1353.	2.2	8
113	Extremely Low Leakage Threshold Switch with Enhanced Characteristics <i>via</i> Ag Doping on Polycrystalline ZnO Fabricated by Facile Electrochemical Deposition for an X-Point Selector. ACS Applied Electronic Materials, 2021, 3, 2309-2316.	2.0	8
114	Threshold voltage instability characteristics under positive dynamic stress in ultrathin HfO2 metal-oxide-semiconductor field-effect transistors. Applied Physics Letters, 2004, 85, 3184-3186.	1.5	7
115	Transient bicarrier response in high-k dielectrics and its impact on transient charge effects in high-k complementary metal oxide semiconductor devices. Applied Physics Letters, 2006, 88, 162905.	1.5	7
116	Impact of flash annealing on performance and reliability of high-κ/metal-gate MOSFETs for sub-45 nm CMOS. , 2007, , .		7
117	Effects of a Gd capping layer on electrical characteristics of metal-oxide-semiconductor field effect transistors with a TaC gate electrode and a HfSiON gate dielectric. Applied Physics Letters, 2009, 95, .	1.5	7
118	Transport property improvements of amorphous Inâ€“Znâ€“O transistors with printed Cu contacts via rapid temperature annealing. Thin Solid Films, 2016, 603, 268-271.	0.8	7
119	Hot carrier reliability of n-MOSFET with ultra-thin HfO/sub 2/ gate dielectric and poly-Si gate. , 0, , .		6
120	High Performance Metal Gate CMOSFETs with Aggressively Scaled Hf-Based High-k. ECS Transactions, 2006, 1, 609-623.	0.3	6
121	A Novel Bias Temperature Instability Characterization Methodology for High-k MOSFETs. Solid-State Device Research Conference, 2008 ESSDERC 2008 38th European, 2006, , .	0.0	6
122	Negative Bias Temperature Instability Dependence on Dielectric Thickness and Nitrogen Concentration in Ultra-scaled HfSiON Dielectric/TiN Gate Stacks. Japanese Journal of Applied Physics, 2006, 45, 2945-2948.	0.8	6
123	Effective surface passivation methodologies for high performance germanium metal oxide semiconductor field effect transistors. Applied Physics Letters, 2008, 93, 192115.	1.5	6
124	â€œSmartâ€•TDDB algorithm for investigating degradation in high-Îº gate dielectric stacks under constant voltage stress. Microelectronic Engineering, 2009, 86, 287-290.	1.1	6
125	Solution-Processed Rb-Doped Indium Zinc Oxide Thin-Film Transistors. IEEE Electron Device Letters, 2018, 39, 1330-1333.	2.2	6
126	Low-Temperature Fabrication of High Quality Gate Insulator in Metalâ€“Oxideâ€“Semiconductor Capacitor Using Laser Annealing. IEEE Electron Device Letters, 2019, 40, 167-170.	2.2	6

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127	Low Temperature and Ion-Cut Based Monolithic 3D Process Integration Platform Incorporated with CMOS, RRAM and Photo-Sensor Circuits. , 2020, , .		6
128	Reliability of High-K Dielectrics and Its Dependence on Gate Electrode and Interfacial / High-K Bi-Layer Structure. Microelectronics Reliability, 2004, 44, 1513-1518.	0.9	5
129	Fast and slow charge trapping/detrapping processes in high-k nMOSFETs. Integrated Reliability Workshop Final Report, 2009 IRW '09 IEEE International, 2006, , .	0.0	5
130	Impact of Nitrogen on PBTI Characteristics of HfSiON/TiN Gate Stacks. , 2006, , .		5
131	Improved Hot Carrier Reliability Characteristics of Metal Oxide Semiconductor Field Effect Transistors with High-k Gate Dielectric by Using High Pressure Deuterium Post Metallization Annealing. Japanese Journal of Applied Physics, 2007, 46, L786.	0.8	5
132	Comparison of On-The-Fly, DC I_{d}â€“V_{g}, and Single-Pulse Methods for Evaluating Threshold Voltage Instability in High-$kappa$ nMOSFETs. IEEE Electron Device Letters, 2007, 28, 245-247.	2.2	5
133	Role of Interfacial Layer on Breakdown of TiN/High-Îº Gate Stacks. Journal of the Electrochemical Society, 2007, 154, G298.	1.3	5
134	Impact of Bottom Interfacial Layer on the Threshold Voltage and Device Reliability of Fluorine Incorporated PMOSFETS with High-K/Metal Gate. , 2007, , .		5
135	Improved Electrical Properties of Solution-Processed ZrO2Gate Dielectric for Large-Area Flexible Electronics. Japanese Journal of Applied Physics, 2013, 52, 100206.	0.8	5
136	Analysis of trap distribution in polysilicon channel transistors using the variable amplitude charge pumping method. Solid-State Electronics, 2015, 104, 86-89.	0.8	5
137	Effects of H2 High-pressure Annealing on HfO2/Al2O3/In0.53Ga0.47As Capacitors: Chemical Composition and Electrical Characteristics. Scientific Reports, 2017, 7, 9769.	1.6	5
138	Significant improvement of conversion efficiency by passivation of low-angle grain boundaries in flexible low-cost single-crystal-like GaAs thin-film solar cells directly deposited on metal tape. Solar Energy Materials and Solar Cells, 2022, 243, 111791.	3.0	5
139	Realiability Characteristics of Metal/High-K Pmos with Top Interface Engineered Band Offset Dielectric (BOD). , 2006, , .		4
140	Device Performance and Reliability Characteristics of Tantalumâ€“Siliconâ€“Nitride Electrode/Hafnium Oxide n-Type Metalâ€“Oxideâ€“Semiconductor Field-Effect Transistor Depending on Electrode Composition. Japanese Journal of Applied Physics, 2009, 48, 116506.	0.8	4
141	Bias dependence of PBTI degradation mechanism in metal-oxide-semiconductor field effect transistors with La-incorporated hafnium-based dielectric. Microelectronic Engineering, 2011, 88, 1373-1375.	1.1	4
142	The electrical and structural properties of HfO2/SrTiO3 stacked gate dielectric with TiN metal gate electrode. Thin Solid Films, 2012, 521, 42-44.	0.8	4
143	Origin of the channel width dependent field effect mobility of graphene field effect transistors. Microelectronic Engineering, 2016, 163, 55-59.	1.1	4
144	Charging effects on reliability of HfO/sub 2/ devices with polysilicon gate electrode. , 0, , .		3

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145	Dynamic positive bias temperature instability characteristics of ultra-thin HfO/sub 2/ NMOSFET. , 0, , .		3
146	High Performing pMOSFETs on Si(110) for Application to Hybrid Orientation Technologies -- Comparison of HfO₂and HfSiON. , 2006, , .		3
147	Decoupling of cold carrier effects in hot carrier reliability of HfO2 gated nMOSFETs. , 2006, , .		3
148	Atomic Layer Deposited HfO2 and HfSiO to Enable CMOS Gate Dielectric Scaling, Mobility, and VTH Stability. ECS Transactions, 2006, 1, 15-28.	0.3	3
149	Effects of gate edge profile on off-state leakage suppresion in metal gate/high-k dielectric n-type metal-oxide-semiconductor field effect transistors. Applied Physics Letters, 2007, 90, 183501.	1.5	3
150	Comparison of La-based high-k dielectrics: HfLaSiON and HfLaON. Microelectronic Engineering, 2009, 86, 268-271.	1.1	3
151	Effect of Fast Components in Threshold-Voltage Shift on Bias Temperature Instability in High-k MOSFETs. IEEE Electron Device Letters, 2010, 31, 287-289.	2.2	3
152	Effect of La incorporation on reliability characteristics of metalâ€“oxide-semiconductor capacitors with hafnium based high-k dielectrics. Microelectronic Engineering, 2012, 89, 31-33.	1.1	3
153	A Novel Combinatorial Approach to the Ferroelectric Properties in Hf x Zr 1âˆ’ x O 2 Deposited by Atomic Layer Deposition. Physica Status Solidi - Rapid Research Letters, 2021, 15, 2100053.	1.2	3
154	Low-Temperature Deep Ultraviolet Laser Polycrystallization of Amorphous Silicon for Monolithic 3-Dimension Integration. IEEE Electron Device Letters, 2021, 42, 784-787.	2.2	3
155	Effects of nitrogen-incorporated interface layer on the transient characteristics of hafnium oxide n-metalâ€“oxideâ€“semiconductor field-effect transistors. Applied Physics Letters, 2005, 86, 123506.	1.5	2
156	Characterization and reliability measurement issues in devices with novel gate stack devices. Thin Solid Films, 2006, 504, 223-226.	0.8	2
157	Charge Trapping Effects in High-k Transistors. ECS Transactions, 2006, 1, 663-670.	0.3	2
158	Comparison of novel BTI measurements for high-k dielectric MOSFETs. , 2006, , .		2
159	Electrical Characterization Methodologies for the Assessment of High-k Gate Dielectric Stacks. ECS Transactions, 2007, 11, 335-346.	0.3	2
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